AMENDMENTS TO THE CLAIMS

The following listing of claims will replace all prior versions, and listings, of claims in this application.

1. (Currently Amended) A system for performing wafer processing, comprising:

an in-line system comprising a stepper for performing alignment and photo-exposure of a wafer and a spinner, in-line connected to the stepper, for performing a coating and development of the wafer; and

an overlay measurement device, in-line connected to the spinner, for automatically measuring an overlay accuracy of the wafer after wafer development is completed by the spinner to determine whether device patterns are accurately aligned.

2. (Original) The system of claim 1, wherein the overlay measurement device is in-line connected to an index arm of the spinner.

3. (Original) The system of claim 2, wherein the wafer is transported from the spinner to the overlay measurement device by bordering input and output pedestals of the spinner and overlay measurement device.

4. (Original) The system of claim 2, wherein the index arm of the spinner directly loads or unloads the wafer on the overlay measurement device.

5. (Original) The system of claim 1, wherein the overlay measurement device further comprises a reject port for discharging a faulty wafer found during an overlay measurement.

6. (Currently Amended) A method for performing wafer processing in a system comprising a stepper, a spinner and an overlay measurement device, comprising the steps of:

aligning and photo-exposing a wafer with the stepper;

coating and developing the wafer with the spinner; and

automatically measuring an overlay accuracy of the wafer with the overlay measurement device after the wafer developing step is completed to determine whether device patterns are accurately aligned, wherein the overlay measurement device is in-line connected to the spinner.

7. (Original) The method of claim 6, wherein the wafer comprises a diameter of at least about 12 inches.

8. (Original) The method of claim 6, wherein the step of measuring the overlay accuracy of the wafer comprises the step of in-line connecting the overlay measurement device to an index arm of the spinner.

9. (Original) The method of claim 8, wherein the step of measuring the overlay accuracy of the wafer further comprises the step of directly loading or unloading the wafer on the overlay measurement device by the index arm of the spinner.

10. (Original) The method of claim 6, wherein the step of measuring the overlay accuracy of the wafer comprises the step of receiving the wafer from the spinner by bordering input and output pedestals of the spinner and the overlay measurement device.

11. (Original) The method of claim 6, wherein the step of measuring the overlay accuracy of the wafer comprises the step of rejecting a faulty wafer.

12. (Currently Amended) A method.for performing wafer processing, comprising the steps of:

performing an in-line process comprising the steps of alignment, photo-exposure, coating and development of a wafer; and

automatically performing an overlay accuracy of the wafer without discharging the wafer after the wafer developing step is completed to determine whether device patterns are accurately aligned.

13. (Original) The method of claim 12, wherein the wafer comprises a diameter of at least about 12 inches.

14. (Original) The method of claim 12, further comprising the step of discharging a faulty wafer found during the step of performing the overlay accuracy of the wafer.